MOSFETs Silicon N-Channel MOS (DTMOSIV)

TK8P60W

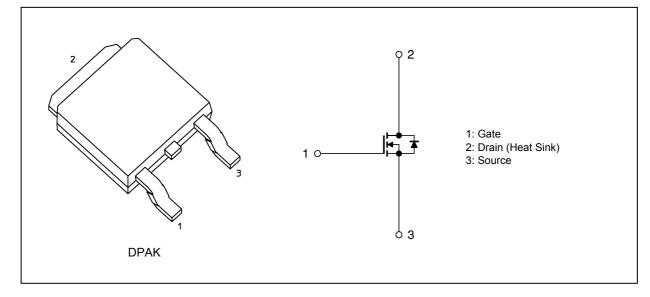
1. Applications

Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 0.42 \Omega$ (typ.) by used to Super Junction Structure : DTMOS
- (2) Easy to control Gate switching
- (3) Enhancement mode: V_{th} = 2.7 to 3.7 V (V_{DS} = 10 V, I_D = 0.4 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25^{\circ}C$ unless otherwise specified)

| Characteristics | Symbol | Rating | Unit | |
|-----------------------------------|----------------------|------------------|------------|----|
| Drain-source voltage | | V _{DSS} | 600 | V |
| Gate-source voltage | | V _{GSS} | ±30 | |
| Drain current (DC) | (Note 1) | Ι _D | 8.0 | Α |
| Drain current (pulsed) | (Note 1) | I _{DP} | 32 | |
| Power dissipation (T _c | _c = 25°C) | PD | 80 | W |
| Single-pulse avalanche energy | (Note 2) | E _{AS} | 105 | mJ |
| Avalanche current | | I _{AR} | 2.0 | A |
| Reverse drain current (DC) | (Note 1) | I _{DR} | 8.0 | |
| Reverse drain current (pulsed) | (Note 1) | I _{DRP} | 32 | |
| Channel temperature | | T _{ch} | 150 | °C |
| Storage temperature | | T _{stg} | -55 to 150 | |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

| Characteristics | Symbol | Мах | Unit |
|------------------------------------|-----------------------|------|------|
| Channel-to-case thermal resistance | R _{th(ch-c)} | 1.57 | °C/W |

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_DD = 90 V, T_ch = 25°C (initial), L = 46.0 mH, R_G = 25 Ω , I_AR = 2.0 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics (Ta = 25°C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|----------------------|---|-----|------|-----|------|
| Gate leakage current | I _{GSS} | V_{GS} = ±30 V, V_{DS} = 0 V | _ | _ | ±1 | μA |
| Drain cut-off current | I _{DSS} | V _{DS} = 600 V, V _{GS} = 0 V | _ | _ | 10 | |
| Drain-source breakdown voltage | V _{(BR)DSS} | I _D = 10 mA, V _{GS} = 0 V | 600 | _ | — | V |
| Gate threshold voltage | V _{th} | V _{DS} = 10 V, I _D = 0.4 mA | 2.7 | — | 3.7 | |
| Drain-source on-resistance | R _{DS(ON)} | V _{GS} = 10 V, I _D = 4.0 A | | 0.42 | 0.5 | Ω |

6.2. Dynamic Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|--------------------|--|-----|------|-----|------|
| Input capacitance | C _{iss} | V_{DS} = 300 V, V_{GS} = 0 V, f = 1 MHz | _ | 570 | _ | pF |
| Reverse transfer capacitance | C _{rss} | | _ | 2.5 | _ | |
| Output capacitance | C _{oss} | | _ | 16 | _ | |
| Effective output capacitance | C _{o(er)} | V_{DS} = 0 to 400 V, V_{GS} = 0 V | _ | 26 | _ | |
| Gate resistance | rg | V _{DS} = OPEN, f = 1 MHz | | 7.5 | _ | Ω |
| Switching time (rise time) | tr | See Figure 6.2.1 | _ | 20 | _ | ns |
| Switching time (turn-on time) | t _{on} |] | | 40 | _ | |
| Switching time (fall time) | t _f |] | | 5.5 | _ | |
| Switching time (turn-off time) | t _{off} | 1 | | 70 | _ | 1 |
| MOSFET dv/dt ruggedness | dv/dt | V _{DD} = 0 to 400 V, I _D = 4.0 A | 50 | _ | _ | V/ns |

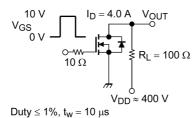


Fig. 6.2.1 Switching Time Test Circuit

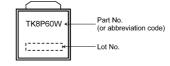
6.3. Gate Charge Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|------------------|---|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Qg | $V_{DD} \approx 400 \text{ V}, V_{GS} \text{ = } 10 \text{V}, \text{I}_{D} \text{ = } 8.0 \text{A}$ | — | 18.5 | — | nC |
| Gate-source charge 1 | Q _{gs1} | | _ | 3.5 | _ | |
| Gate-drain charge | Q _{gd} | | | 9.0 | _ | |

6.4. Source-Drain Characteristics (T_a = 25°C unless otherwise specified)

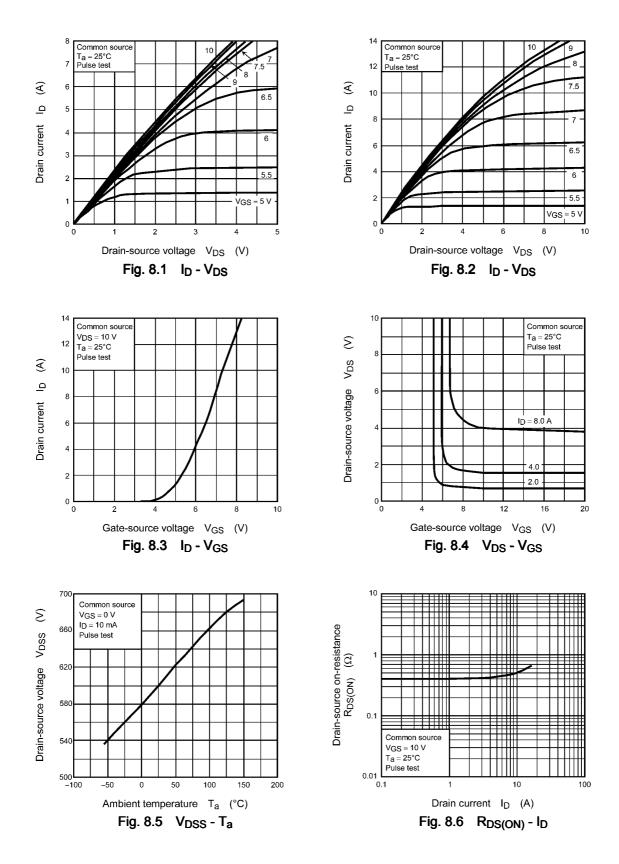
| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|-------------------------------|------------------|---|-----|------|------|------|
| Diode forward voltage | V _{DSF} | I _{DR} = 8.0 A, V _{GS} = 0 V | _ | _ | -1.7 | V |
| Reverse recovery time | t _{rr} | I _{DR} = 4.0 A, V _{GS} = 0 V | | 230 | _ | ns |
| Reverse recovery charge | Q _{rr} | -dI _{DR} /dt = 100 A/μs | _ | 1.9 | _ | μC |
| Peak reverse recovery current | l _{rr} | | | 17 | _ | А |
| Diode dv/dt ruggedness | dv/dt | I _{DR} = 4.0 A, V _{GS} = 0 V, V _{DD} = 400 V | 15 | _ | | V/ns |

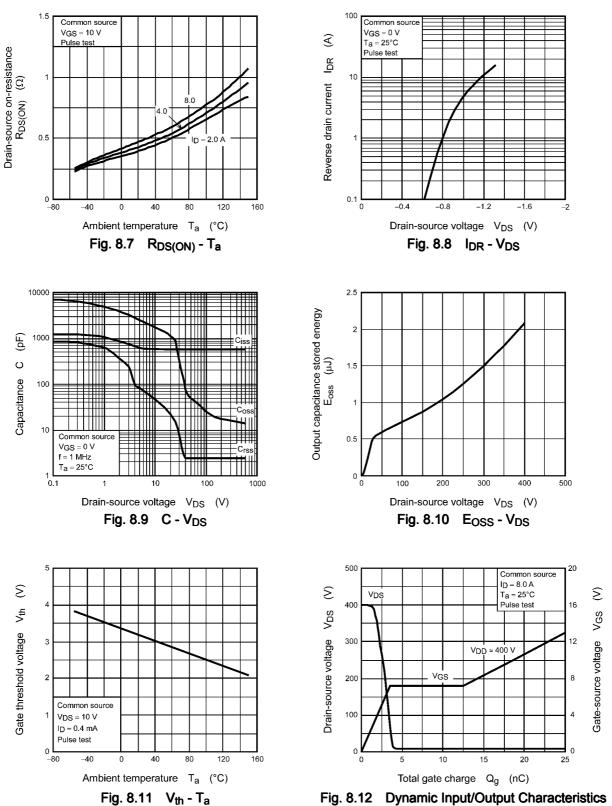
7. Marking





8. Characteristics Curves (Note)





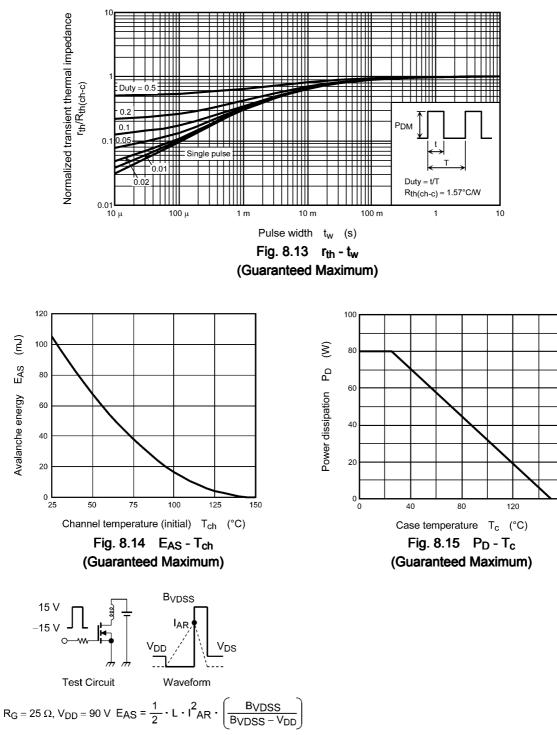
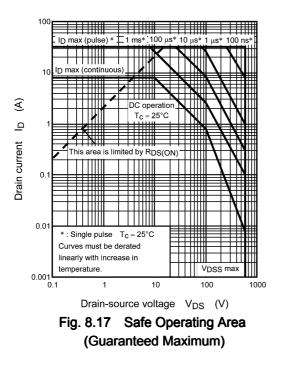


Fig. 8.16 Test Circuit/Waveform

160



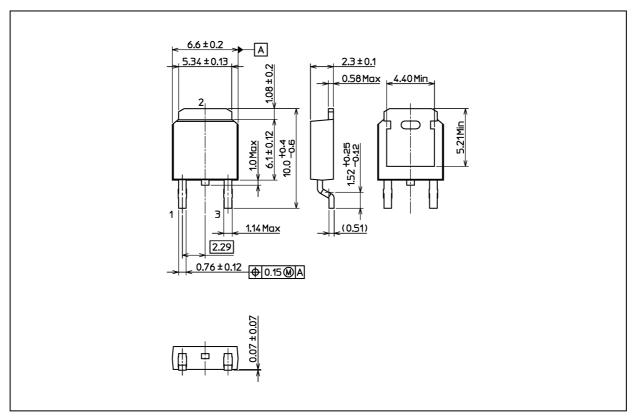
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



TK8P60W

Package Dimensions

Unit: mm



Weight: 0.36 g (typ.)

| | Package Name(s) | |
|-----------------|-----------------|--|
| TOSHIBA: 2-7K1S | | |
| Nickname: DPAK | | |

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